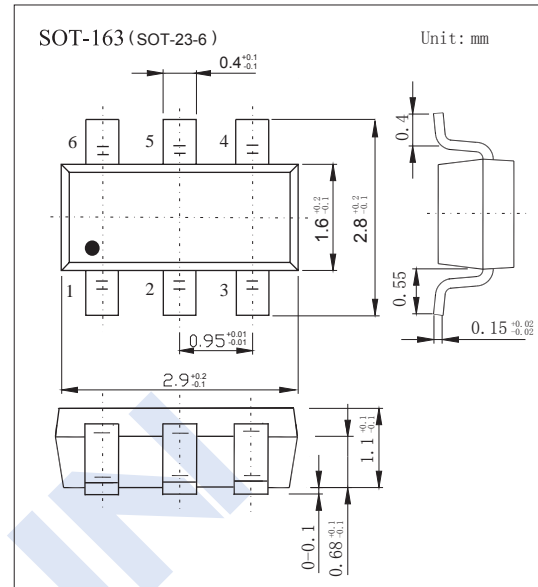
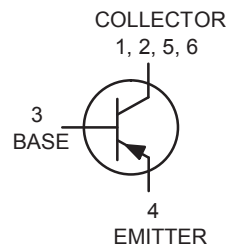


PNP Transistors

2KA7031DV

■ Features

- Collector Current Capability $I_C = -2A$
- Collector Emitter Voltage $V_{CE0} = -35V$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-55	V
Collector - Emitter Voltage	V_{CE0}	-35	
Emitter - Base Voltage	V_{EB0}	-6	
Collector Current - Continuous	I_C	-2	A
Peak Collector Current	I_{CM}	-5	
Collector Power Dissipation (Note.1) (Note.2) Single Pulse < 10 sec (Note.2)	P_C	625	mW
		1	
		1.75	W
Thermal Resistance From Junction To Ambient (Note.1) (Note.2)	$R_{\theta JA}$	200	$^\circ C/W$
		120	
Thermal Resistance From Junction To Lead	$R_{\theta JL}$	80	
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature range	T_{stg}	-55 to 150	

Note.1:FR-4 @ Minimum Pad

Note.2:FR-4 @ 1.0 X 1.0 inch Pad

PNP Transistors

2KA7031DV

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = -100 μA, I _E =0	-55			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = -1 mA, I _B =0	-35			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _c =0	-6			
Collector-base cut-off current	I _{CB0}	V _{CB} = -35 V, I _E =0			-100	nA
Collector- emittercut-off current	I _{CES}	V _{CE} = -35 V, I _E =0			-100	
Emitter cut-off current	I _{EB0}	V _{EB} = -4V, I _c =0			-100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-800 mA, I _B =-80mA			-0.12	V
		I _c =-1.2 A, I _B =-120mA			-0.18	
		I _c =-2 A, I _B =-200mA			-0.25	
Base - emitter saturation voltage	V _{BE(sat)}	I _c =-1.2 A, I _B =-12 mA			-0.85	
Base-emitter turn-on voltage	V _{BE(on)}	V _{CE} = -1.2V, I _c = -500mA			-0.875	
DC current gain	h _{FE}	V _{CE} = -1.2V, I _c = -500mA	200		400	
Transition frequency	f _T	V _{CE} = -5V, I _c = -100mA, f=100MHz	100			MHz

Note.: Pulsed Condition: Pulse Width = 300us, Duty Cycle ≤ 2%

■ Marking

Marking	2G
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